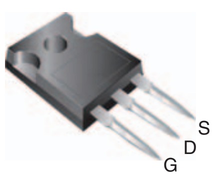
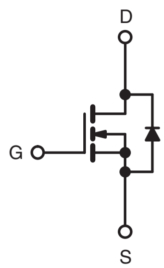
# Power MOSFET

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) | 200 | |
| $R_{DS(on)}$ (Ω) | $V_{GS}$ = 10 V | 0.085 |
| $Q_g$ (Max.) (nC) | 140 | |
| $Q_{gs}$ (nC) | 28 | |
| $Q_{gd}$ (nC) | 74 | |
| Configuration | Single | |

TO-247




N-Channel MOSFET

## FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available

Pb Available

RoHS* COMPLIANT

## DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.
The TO-220 package is universially preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

| ORDERING INFORMATION | |
|---|---|
| Package | TO-247 |
| Lead (Pb)-free | IRFP250PbF |
| | SiHFP250-E3 |
| SnPb | IRFP250 |
| | SiHFP250 |

**ABSOLUTE MAXIMUM RATINGS** $T_C$ = 25 °C, unless otherwise noted

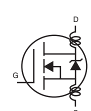
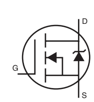
| PARAMETER | | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DS}$ | 200 | V |
| Gate-Source Voltage | | | $V_{GS}$ | ± 20 | |
| Continuous Drain Current | $V_{GS}$ at 10 V | $T_C$ = 25 °C | $I_D$ | 30 | A |
| | | $T_C$ = 100 °C | | 19 | |
| Pulsed Drain Current[a] | | | $I_{DM}$ | 120 | |
| Linear Derating Factor | | | | 1.5 | W/°C |
| Single Pulse Avalanche Energy[b] | | | $E_{AS}$ | 410 | mJ |
| Repetitive Avalanche Current[a] | | | $I_{AR}$ | 30 | A |
| Repetitive Avalanche Energy[a] | | | $E_{AR}$ | 19 | mJ |
| Maximum Power Dissipation | $T_C$ = 25 °C | | $P_D$ | 190 | W |
| Peak Diode Recovery dV/dt[c] | | | dV/dt | 5.0 | V/ns |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | - 55 to + 150 | °C |
| Soldering Recommendations (Peak Temperature) | for 10 s | | | 300[d] | |
| Mounting Torque | 6-32 or M3 screw | | | 10 | lbf · in |
| | | | | 1.1 | N · m |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. $V_{DD}$ = 50 V, starting $T_J$ = 25 °C, L = 683 µH, $R_G$ = 25 Ω, $I_{AS}$ = 30 A (see fig. 12).
c. $I_{SD} \leq 30$ A, dI/dt ≤ 190 A/µs, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
d. 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TYP.** | **MAX.** | **UNIT** |
| Maximum Junction-to-Ambient | $R_{thJA}$ | - | 40 | °C/W |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | 0.24 | - | |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | - | 0.65 | |

| **SPECIFICATIONS** $T_J$ = 25 °C, unless otherwise noted | | | | | | |
|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 200 | - | - | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C, $I_D$ = 1 mA | - | 0.27 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 2.0 | - | 4.0 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ± 20 V | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V | - | - | 25 | µA |
| | | $V_{DS}$ = 160 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | - | - | 250 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V; $I_D$ = 18 A[b] | - | - | 0.085 | Ω |
| Forward Transconductance | $g_{fs}$ | $V_{DS}$ = 50 V, $I_D$ = 18 A | 12 | - | - | S |
| **Dynamic** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1.0 MHz, see fig. 5 | - | 2800 | - | pF |
| Output Capacitance | $C_{oss}$ | | - | 780 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 250 | - | |
| Total Gate Charge | $Q_g$ | $V_{GS}$ = 10 V; $I_D$ = 30 A, $V_{DS}$ = 160 V, see fig. 6 and 13[b] | - | - | 140 | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | - | 28 | |
| Gate-Drain Charge | $Q_{gd}$ | | - | - | 74 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 100 V, $I_D$ = 30 A, $R_G$ = 6.2 Ω, $R_D$ = 3.2 Ω, see fig. 10[b] | - | 16 | - | ns |
| Rise Time | $t_r$ | | - | 86 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 70 | - | |
| Fall Time | $t_f$ | | - | 62 | - | |
| Internal Drain Inductance | $L_D$ | Between lead, 6 mm (0.25") from package and center of die contact  | - | 5.0 | - | nH |
| Internal Source Inductance | $L_S$ | | - | 13 | - | |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 30 | A |
| Pulsed Diode Forward Current[a] | $I_{SM}$ | | - | - | 120 | |
| Body Diode Voltage | $V_{SD}$ | $T_J$ = 25 °C, $I_S$ = 30 A, $V_{GS}$ = 0 V[b] | - | - | 2.0 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = 30 A, dI/dt = 100 A/µs | - | 360 | 540 | ns |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | - | 4.6 | 6.9 | µC |
| Forward Turn-On Time | $t_{on}$ | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$) | | | | |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

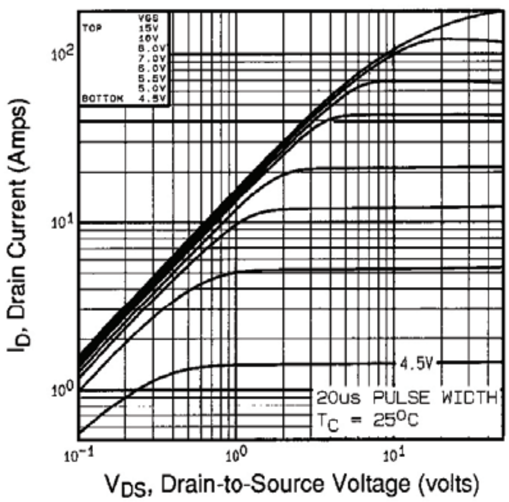



Fig. 1 - Typical Output Characteristics, $T_C$ = 25 °C

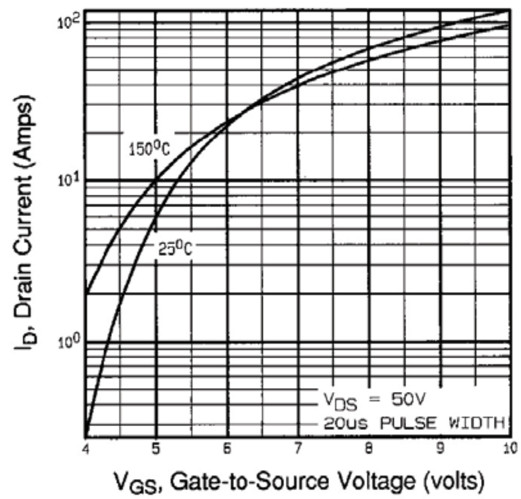



Fig. 3 - Typical Transfer Characteristics

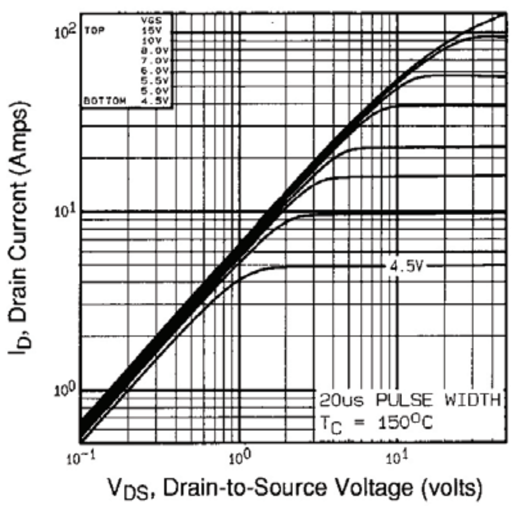



Fig. 2 -Typical Output Characteristics, $T_C$ = 150 °C

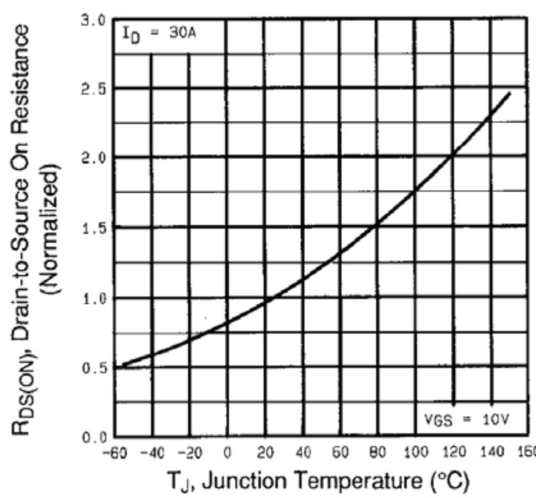



Fig. 4 - Normalized On-Resistance vs. Temperature

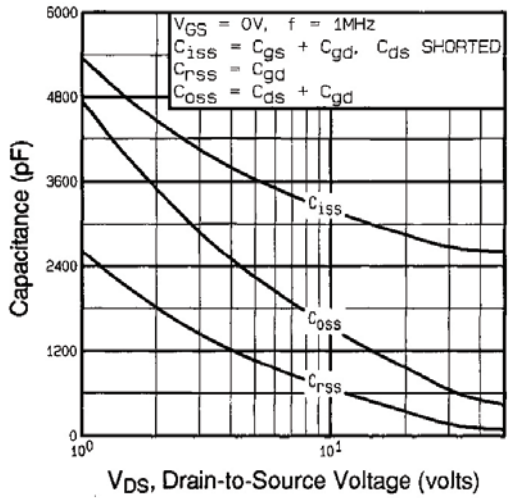



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

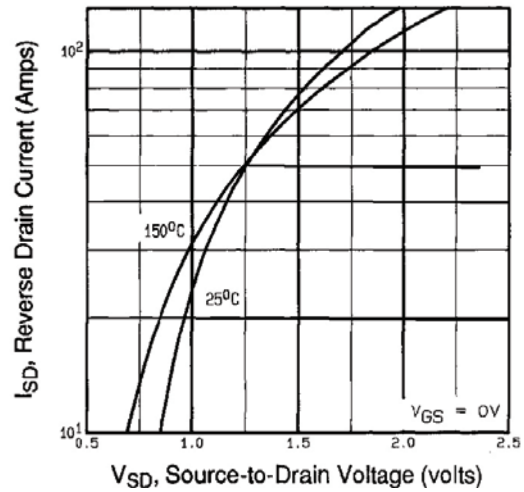



Fig. 7 - Typical Source-Drain Diode Forward Voltage

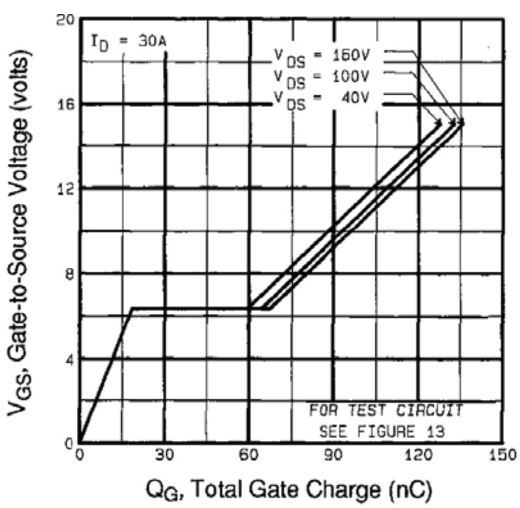



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

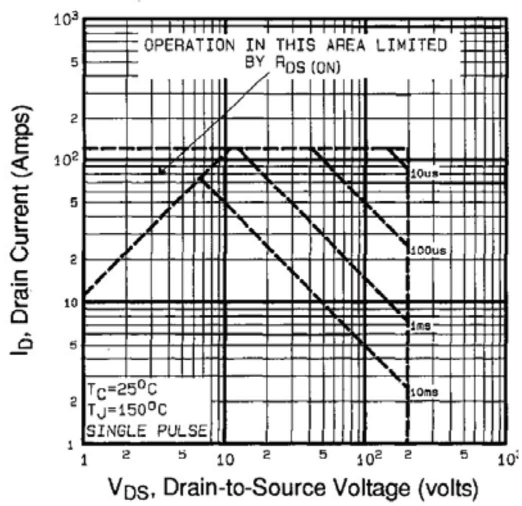



Fig. 8 - Maximum Safe Operating Area

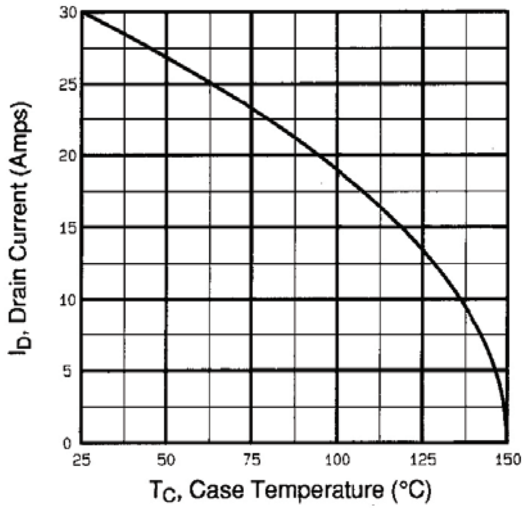



Fig. 9 - Maximum Drain Current vs. Case Temperature

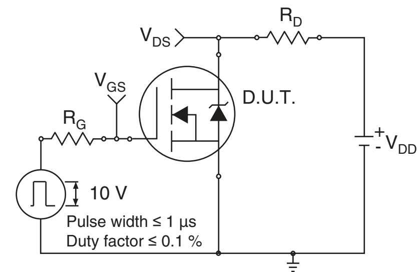



Fig. 10a - Switching Time Test Circuit

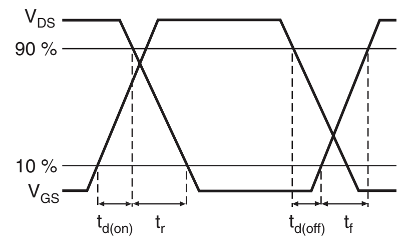



Fig. 10b - Switching Time Waveforms

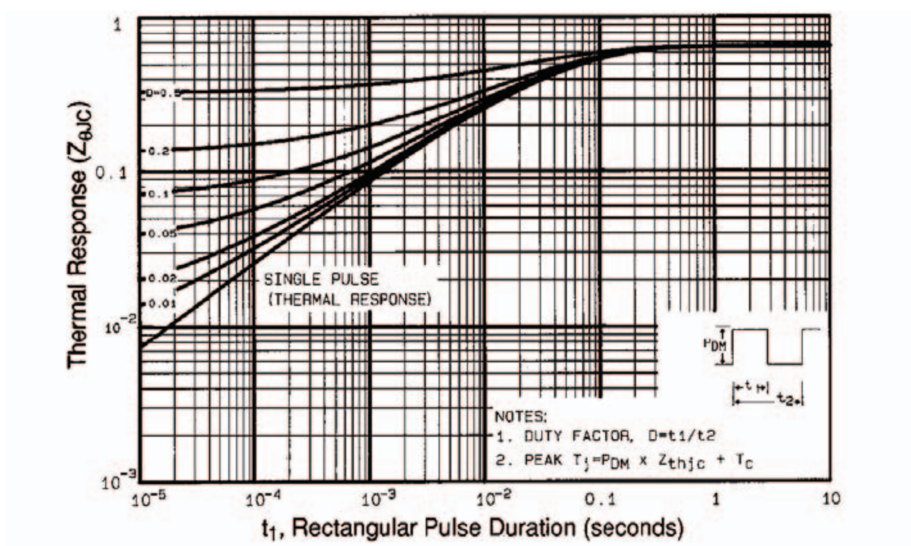



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

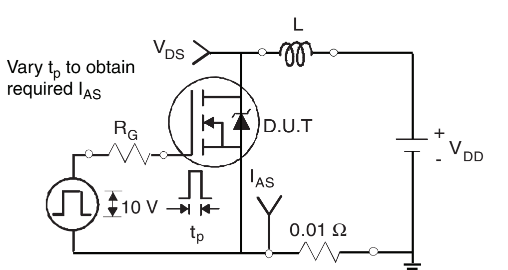



Fig. 12a - Unclamped Inductive Test Circuit

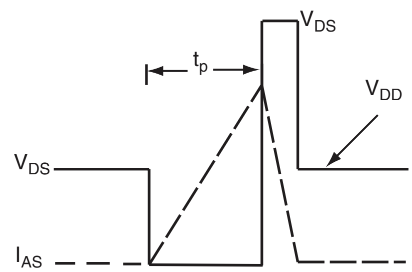



Fig. 12b - Unclamped Inductive Waveforms

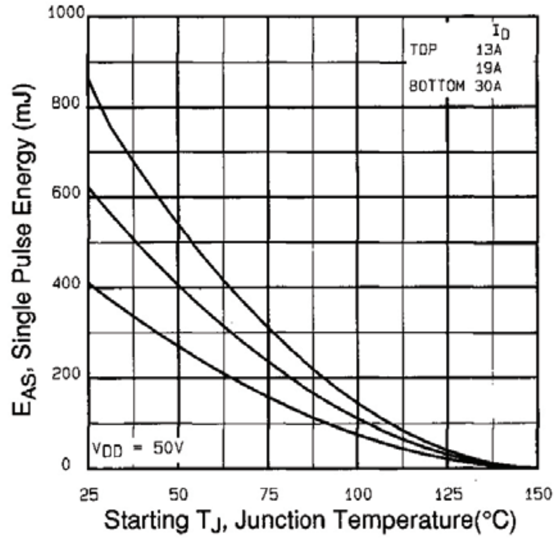



Fig. 12c - Maximum Avalanche Energy vs. Drain Current

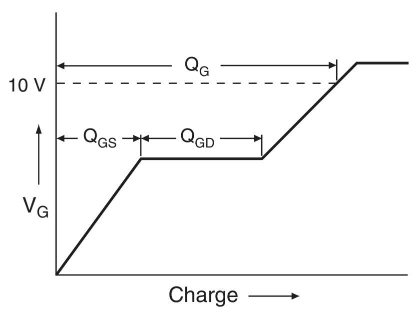



Fig. 13a - Basic Gate Charge Waveform

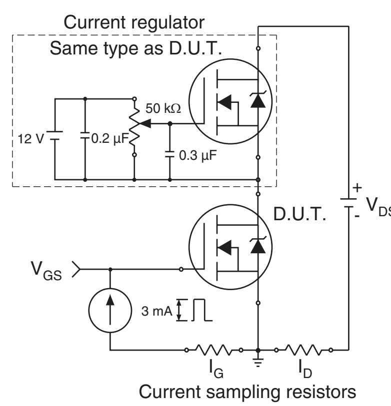



Fig. 13b - Gate Charge Test

## Peak Diode Recovery dV/dt Test Circuit

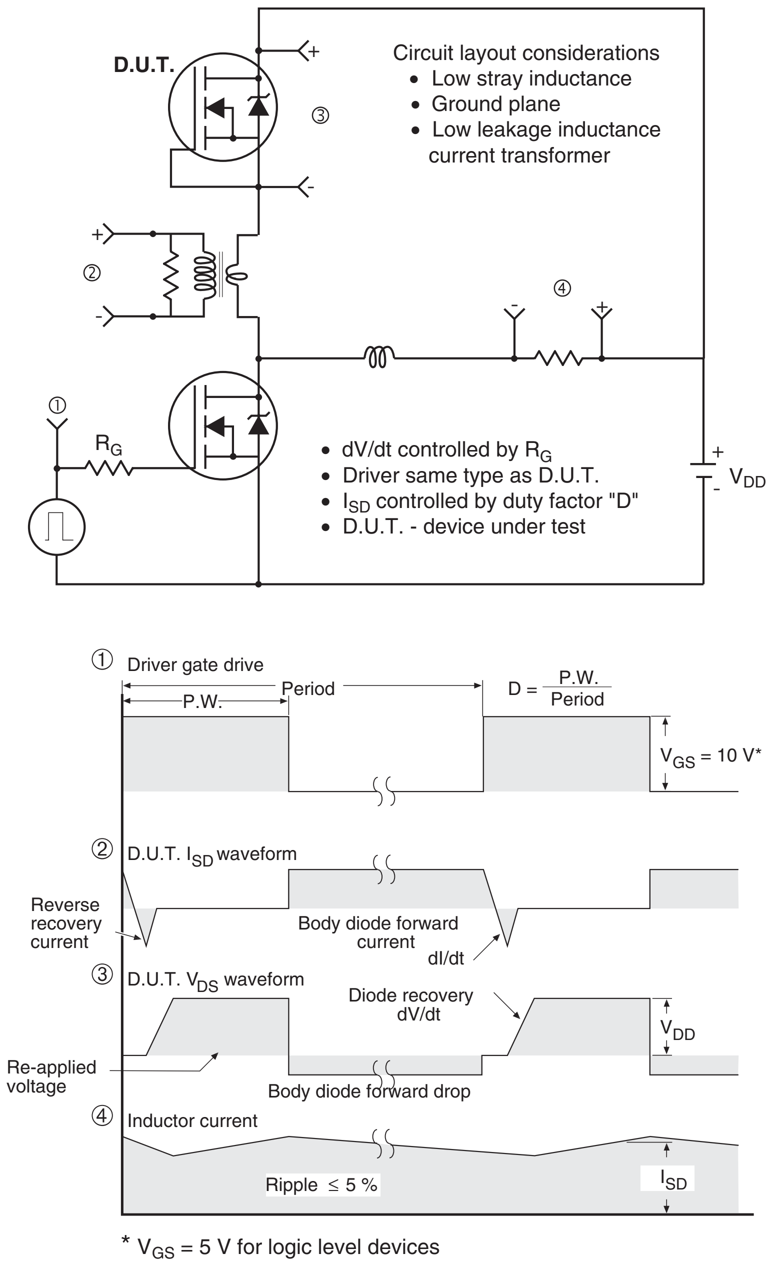



**Fig. 14 - For N-Channel**

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